Front Matter: Volume 8681
Contents

  xv Conference Committee
  xix Introduction
  xxi The Diana Nyyssonen Memorial Award for Best Paper

Part One

KEYNOTE SESSION

8681 02 Metrology in times of shrinking budgets (Keynote Paper) [8681-1]
W. H. Arnold, ASML USA Inc. (United States)

METROLOGY FOR PROCESS CONTROL

8681 03 Implementation of hybrid metrology at HVM fab for 20nm and beyond (Invited Paper) [8681-2]
GLOBALFOUNDRIES (United States); C. Hartig, GLOBALFOUNDRIES (Germany); B. C. Kang,
C. Bozdag, M. Sendelbach, P. Isbester, Nova Measuring Instruments, Inc. (United States);
L. Issascharoff, Nova Measuring Instruments Ltd. (Israel)

8681 04 On-product overlay enhancement using advanced litho-cluster control based on
integrated metrology, ultra-small DBO targets and novel corrections [8681-3]
K. Bhattacharyya, ASML Netherlands B.V. (Netherlands); C.-M. Ke, G.-T. Huang, K.-H. Chen,
Taiwan Semiconductor Manufacturing Co., Ltd. (Taiwan); H.-J. H. Smilde, A. Fuchs, M. Jak,
M. van Schijndel, M. Bozkurt, M. van der Schaar, S. Meyer, M. Un, S. Morgan, J. Wu, V. Tsai,
F. Liang, A. den Boef, P. ten Berge, M. Kubis, C. Wang, C. Fouquet, ASML Netherlands B.V.
(Netherlands); L.-G. Terng, D. Hwang, K. Cheng, T.-S. Gau, Y. C. Ku, Taiwan Semiconductor
Manufacturing Co., Ltd. (Taiwan)

8681 05 Toward 7nm target on product overlay for C028 FDSOI technology [8681-4]
M. Gatefait, B. Le-Gratiet, P. J. Goirand, A. Lam, STMicroelectronics (France); R. Van Haren,
A. Pastol, M. Doytcheva, X. L. Liu, J. Beltman, ASML Netherlands B.V. (Netherlands)

8681 06 Introduction of next-generation 3D AFM for advanced process control [8681-5]
(Korea, Republic of)

8681 07 High-volume process monitoring of FEOL 22nm FinFET structures using an automated STEM
[8681-6]
O. Ugurlu, M. Strauss, G. Dutrow, J. Blackwood, B. Routh, Jr., C. Senowitz, P. Plachinda,
R. Alvis, FEI Co. (United States)
DESIGN-BASED METROLOGY AND PROCESS CONTROL

8681 08 Material contrast based inline metrology: process verification and control using back scattered electron imaging on CD-SEM (Invited Paper) [8681-7]
C. Hartig, D. Fischer, B. Schulz, GLOBALFOUNDRIES (Germany); A. Vaid, GLOBALFOUNDRIES (United States); O. Adan, S. Levi, A. Ge, J. Zhou, M. Bar-Zvi, Applied Materials (Israel); R. Enge, U. Groh, Applied Materials (Germany)

8681 09 When things go pear shaped: contour variations of contacts [8681-8]
C. Utzny, Advanced Mask Technology Ctr. GmbH Co. KG (Germany)

8681 0A Measurement technology to quantify 2D pattern shape in sub-2x nm advanced lithography [8681-9]
D. Fuchimoto, H. Sakai, H. Shindo, M. Izawa, H. Sugahara, Hitachi High-Technologies Corp. (Japan); J. Van de Kerkhove, P. De Bisschop, IMEC (Belgium)

8681 0B Defect window analysis by using SEM-contour based shape quantifying method for sub-20mm node production [8681-10]
D. Hibino, Hitachi High-Technologies Corp. (Japan); M. Hsu, Hitachi High-Technologies Corp. (Taiwan); H. Shindo, M. Izawa, Y. Enomoto, Hitachi High-Technologies Corp. (Japan); J. F. Lin, J. R. Hu, Taiwan Semiconductor Manufacturing Co., Ltd. (Taiwan)

8681 0C A framework for exploring the interaction between design rules and overlay control [8681-11]
R. S. Ghaida, GLOBALFOUNDRIES (United States); M. Gupta, P. Gupta, Univ. of California, Los Angeles (United States)

INSPECTION

8681 0D In-line E-beam wafer metrology and defect inspection: the end of an era for image-based critical dimensional metrology? New life for defect inspection (Invited Paper) [8681-12]
E. Solecky, O. D. Patterson, A. Stamper, IBM Systems and Technology Group (United States); E. McLellan, IBM Albany Nanotech (United States); R. Buengener, A. Vaid, GLOBALFOUNDRIES (United States); C. Hartig, GLOBALFOUNDRIES (Germany); B. Bunday, A. Arceo, A. Cepler, SEMATECH (United States)

8681 0E Enhancing 9nm node dense patterned defect optical inspection using polarization, angle, and focus [8681-13]
B. M. Barnes, F. Goasmat, M. Y. Sohn, H. Zhou, R. M. Silver, National Institute of Standards and Technology (United States); A. Arceo, SEMATECH (United States)

8681 0F Capturing buried defects in metal interconnections with electron beam inspection system [8681-14]
H. Xiao, X. Jiang, D. Trease, M. Van Riet, S. Ramprasad, A. Bhatia, P. Lefebvre, D. Bastard, O. Moreau, C. Maher, P. MacDonald, C. Campochiaro, KLA-Tencor Corp. (United States)

8681 0G 22nm node wafer inspection using diffraction phase microscopy and image post-processing [8681-15]
R. Zhou, G. Popescu, L. L. Goddard, Univ. of Illinois at Urbana-Champaign (United States)
8681 0H  Coherent diffractive imaging microscope with a tabletop high harmonic EUV source
[B8681-17]
B. Zhang, M. D. Seaberg, D. E. Adams, D. F. Gardner, M. M. Murnane, H. C. Kapteyn, Univ. of Colorado at Boulder (United States)

8681 0I  Fin stress and pitch measurement using x-ray diffraction reciprocal space maps and optical scatterometry [B8681-124]
A. C. Diebold, M. Medikonda, G. R. Muthinti, Univ. at Albany (United States); V. K. Kamineni, J. Fronheiser, GLOBALFOUNDRIES (United States); M. Wormington, Jordan Valley Semiconductors, Inc. (United States); B. Peterson, J. Race, Nanometrics Inc. (United States)

ACCELERATED DEVELOPMENT OF MATERIALS AND PROCESSES: JOINT SESSION WITH CONFERENCES 8681 AND 8682

8681 0J  Photoresist shrinkage effects in 16nm node extreme ultraviolet (EUV) photoresist targets [B8681-18]
B. Bunday, C. Montgomery, SEMATECH (United States); W. Montgomery, Univ. at Albany (United States); A. Cepler, SEMATECH (United States) and Univ. at Albany (United States)

8681 0K  Precise measurement of photoresist cross-sectional shape change caused by SEM-induced shrinkage [B8681-19]
T. Ohashi, T. Sekiguchi, A. Yamaguchi, J. Tanaka, Hitachi Ltd. (Japan); H. Kawada, Hitachi High-Technologies Corp. (Japan)

NEW HORIZONS

8681 0L  Critical dimension small angle x-ray scattering measurements of FinFET and 3D memory structures [B8681-20]
C. Settens, Univ. at Albany (United States); B. Bunday, SEMATECH (United States); B. Thiel, Univ. at Albany (United States) and SEMATECH (United States); R. J. Kline, D. Sunday, C. Wang, W.-L. Wu, National Institute of Standards and Technology (United States); R. Matyi, Univ. at Albany (United States)

8681 0M  Mueller based scatterometry measurement of nanoscale structures with anisotropic in-plane optical properties (Best Student Paper Award) [B8681-21]
G. R. Muthinti, M. Medikonda, Univ. at Albany (United States); J. Fronheiser, V. K. Kamineni, GLOBALFOUNDRIES (United States); B. Peterson, J. Race, Nanometrics Inc. (United States); A. C. Diebold, Univ. at Albany (United States)

8681 0N  Probing limits of acoustic nanometrology using coherent extreme ultraviolet light [B8681-22]
D. Nardi, K. M. Hoogeboom-Pot, J. N. Hernandez-Charpak, JILA (United States); M. Tripp, S. W. King, Intel Corp. (United States); E. H. Anderson, Lawrence Berkeley National Lab. (United States); M. M. Murnane, H. C. Kapteyn, JILA (United States)

8681 0O  Nanoscale modulus and surface chemistry characterization for collapse free resists [B8681-23]
P. K. Kulshreshtha, Lawrence Berkeley National Lab. (United States); K. Maruyama, JSR Micro, Inc. (United States); S. Kiani, D. Ziegler, Lawrence Berkeley National Lab. (United States); J. Blackwell, Intel Corp. (United States); D. Olynick, P. D. Ashby, Lawrence Berkeley National Lab. (United States)
Photoluminescence metrology for LED characterization in high volume manufacturing [8681-24]
C. J. Raymond, Z. Li, Nanometrics Inc. (United States)

SCATTEROMETRY

Intercomparison between optical and x-ray scatterometry measurements of FinFET structures [8681-25]
P. Lemailliet, Univ. of Maryland (United States) and National Institute of Standards and Technology (United States); T. A. Germer, R. J. Kline, D. F. Sunday, C. Wang, W.-L. Wu, National Institute of Standards and Technology (United States)

28nm FD-SOI metal gate profile optimization, CD and undercut monitoring using scatterometry measurement [8681-26]
R. Bouyssou, B. Le Gratiet, P. Gouraud, STMicroelectronics (France); L. Desvoivres, CEA-LETI (France); G. Briend, IBM (France) and Dolphin Integration (France); B. Dumont, STMicroelectronics (France)

Evaluating scatterometry 3D capabilities for EUV [8681-27]
J. Li, Nanometrics Inc. (United States); O. Kritsun, GLOBALFOUNDRIES (United States); P. Dasari, Nanometrics Inc. (United States); C. Volkman, T. Wallow, GLOBALFOUNDRIES (United States); J. Hu, Z. Liu, Nanometrics Inc. (United States)

Scatterometry evaluation of focus-dose effects of EUV structures [8681-28]
P. Dasari, Nanometrics Inc. (United States); O. Kritsun, GLOBALFOUNDRIES (United States); J. Li, Nanometrics Inc. (United States); C. Volkman, GLOBALFOUNDRIES (United States); J. Hu, Z. Liu, Nanometrics Inc. (United States)

Direct-scatterometry-enabled optical-proximity-correction-model calibration [8681-115]
C.-Y. Chen, P. C. W. Ng, C.-H. Liu, Y.-T. Shen, K.-Y. Tsai, J.-H. Li, National Taiwan Univ. (Taiwan); J. J. Shieh, A. C. Chen, ASML Taiwan Ltd. (Taiwan)

Enhancing scatterometry CD signal-to-noise ratio for 1x logic and memory challenges [8681-122]
D. Shaughnessy, S. Krishnan, L. Wei, A. V. Shchegrov, KLA-Tencor Corp. (United States)

The correlation between ArF resist dispense volume and surface tension [8681-59]
T.-C. Kuo, United Microelectronics Corp. (Taiwan)

Enhanced photomask quality control by 2D structures monitoring using auto image-to-layout method on advanced 28nm technology node or beyond [8681-60]
E. Guo, I. Shi, E. Tian, Semiconductor Manufacturing International Corp. (China); C. Hsiang, Anchor Semiconductor, Inc. (United States); G. Cheng, L. Ling, S. Chen, Anchor Semiconductor, Inc. (China); Y. Chen, Anchor Semiconductor, Inc. (United States); K. Zhou, Anchor Semiconductor, Inc. (China); J. Wu, K. Wu, Anchor Semiconductor, Inc. (United States)
High order wafer alignment for 20nm node logic process [8681-63]
B. Jeon, S. Pal, S. Mehta, S. Lokesh, Y. T. Jiang, C. Li, M. Yelverton, Y. Wei,
GLOBALFOUNDRIES (United States)

In-die overlay metrology method using defect review SEM images [8681-64]
J. Oh, G. Kwon, D. Mun, H. Yoo, S. Kim, T.-H. Kim, SK Hynix, Inc. (Korea, Republic of);
M. Harada, Y. Minekawa, Hitachi, Ltd. (Japan); F. Fukunaga, M. Nozoe, Hitachi High-
Technologies Corp. (Japan)

Control of inspection for EUV substrates and mask blanks [8681-65]
M. Godwin, T. Ranganath, A. Ma, SEMATECH (United States)

Joint calibration of 3D resist image and CDSEM [8681-66]
C. S. Chou, Y. Y. He, Y. P. Tang, Y. T. Chang, W. C. Huang, R. G. Liu, T. S. Gau, Taiwan
Semiconductor Manufacturing Co., Ltd. (Taiwan)

Line edge roughness measurement technique for fingerprint pattern in block copolymer
thin film [8681-67]
M. Isawa, Hitachi High-Technologies Corp. (Japan); K. Sakai, Hitachi High-Technologies
Corp. (Japan) and IMEC (Belgium); P. A. Rincon Delgadillo, IMEC (Belgium) and The Univ.
of Chicago (United States); R. Gronheid, IMEC (Belgium); H. Yoshiida, Hitachi, Ltd. (Japan)

Increased particle inspection sensitivity by reduction of background scatter variance
[8681-72]
P. van der Walle, P. Kumar, D. Ityakov, R. Versluis, D. J. Maas, O. Kievit, J. Janssen,
J. C. J. van der Donck, TNO (Netherlands)

Overlay improvement through lot-based feed-forward: applications to various 28nm node
lithography operations [8681-73]
B. Orlando, M. Gatefait, J. De-Caunes, P. J. Goirand, STMicroelectronics (France)

Scatterometry-based dose and focus decorrelation: applications to 28nm contact holes
patterning intrafield focus investigations [8681-74]
B. Orlando, N. Spaziani, N. Socquet, R. Bouyssou, M. Gatefait, P. J. Goirand,
STMicroelectronics (France)

Fast simulation method for parameter reconstruction in optical metrology [8681-75]
S. Burger, Zuse Institute Berlin (Germany) and JCMwave GmbH (Germany); L. Zschiegich,
J. Pomplun, JCMwave GmbH (Germany); F. Schmidt, Zuse Institute Berlin (Germany) and
JCMwave GmbH (Germany); B. Bodermann, Physikalisch-Technische Bundesanstalt
(Germany)

DSA hole defectivity analysis using advanced optical inspection tool [8681-76]
R. Harukawa, M. Aoki, A. Cross, V. Nagawami, KLA-Tencor Corp. (United States); T. Tomita,
Tokyo Electron Kyushu Ltd. (Japan); S. Nagahara, Tokyo Electron Ltd. (Japan);
M. Muramatsu, S. Kawakami, H. Kosugi, Tokyo Electron Kyushu Ltd. (Japan); B. Rathsack,
Tokyo Electron America, Inc. (United States); T. Kitano, Tokyo Electron Kyushu Ltd. (Japan);
J. Sweis, A. Mokhberi, Cadence Design Systems, Inc. (United States)
<table>
<thead>
<tr>
<th>Conf. Paper ID</th>
<th>Title</th>
<th>Authors</th>
</tr>
</thead>
<tbody>
<tr>
<td>8681 1B</td>
<td><strong>Scatterometry simulator development with GPU, real-coded GA and RCWA</strong> [8681-78]</td>
<td>H. Shirasaki, Tamagawa Univ. (Japan)</td>
</tr>
<tr>
<td>8681 1C</td>
<td><strong>In-line high-K/metal gate monitoring using picosecond ultrasonics</strong> [8681-79]</td>
<td>C. W. Hsu, R. P. Huang, United Microelectronics Corp. (Taiwan); J. Chen, J. Tan, Rudolph Technologies Taiwan (Taiwan); H. F. Huang, W. Lin, Y. L. Hsieh, W. C. Tsao, C. H. Chen, Y. M. Lin, C. H. Lin, H. K. Hsu, K. Liu, C. C. Huang, J. Y. Wu, United Microelectronics Corp. (Taiwan); J. Dai, P. Mukundhan, Rudolph Technologies, Inc. (United States)</td>
</tr>
<tr>
<td>8681 1D</td>
<td><strong>Advanced overlay stability control with correction per exposure on immersion scanners</strong> [8681-80]</td>
<td>J. Han, J. Heo, C. Hwang, J. Yeo, SAMSUNG Electronics Co., Ltd. (Korea, Republic of)</td>
</tr>
<tr>
<td>8681 1F</td>
<td><strong>Performance of ASML YieldStar µDBO overlay targets for advanced lithography nodes C028 and C014 overlay process control</strong> [8681-83]</td>
<td>Y. Blancquaert, CEA-LETI (France); C. Dezauzier, STMicroelectronics (France); J. Depre, M. Mqiyyass, J. Bellman, ASML Netherlands B.V. (Netherlands)</td>
</tr>
<tr>
<td>8681 1G</td>
<td><strong>Overlay accuracy calibration</strong> [8681-84]</td>
<td>E. Amit, D. Klein, G. Cohen, N. Amir, M. Har-Zvi, KLA-Tencor (Israel); C. Kato, H. Kurita, KLA-Tencor (Japan)</td>
</tr>
<tr>
<td>8681 1H</td>
<td><strong>A novel focus monitoring technique using Iso-Dense overlay mark</strong> [8681-85]</td>
<td>S. X. Li, J. R. Cheng, A. Bourov, G. Sun, Shanghai Micro Electronics Equipment Co., Ltd. (China)</td>
</tr>
<tr>
<td>8681 1I</td>
<td><strong>Manufacturing and advanced characterization of sub-25nm diameter CD-AFM probes with sub-10nm tip edges radius</strong> [8681-86]</td>
<td>J. Foucher, CEA-LETI (France); P. Filippov, C. Penzkofer, B. Irmer, S. W. Schmidt, nanotools GmbH (Germany)</td>
</tr>
<tr>
<td>8681 1J</td>
<td><strong>Quality metric for accurate overlay control in &lt;20nm nodes</strong> [8681-87]</td>
<td>D. Klein, E. Amit, G. Cohen, N. Amir, M. Har-Zvi, KLA-Tencor (Israel); C.-C. K. Huang, R. Karur-Shanmugam, B. Pierson, KLA-Tencor Corp. (United States); C. Kato, H. Kurita, KLA-Tencor (Japan)</td>
</tr>
<tr>
<td>8681 1K</td>
<td><strong>SEM-contour shape analysis method for advanced semiconductor devices</strong> [8681-88]</td>
<td>Y. Toyoda, Hitachi, Ltd. (Japan); H. Shindo, Y. Ota, R. Matsuoka, Y. Hojo, D. Fuchimoto, D. Hibino, H. Sakai, Hitachi High-Technologies Corp. (Japan)</td>
</tr>
</tbody>
</table>
Part Two

8681 1M **Sensitivity improvement by a hybrid scatterometer** [8681-90]
H. Lu, F. Wang, L. Duan, Y. Chen, Shanghai Micro Electronics Equipment Co., Ltd. (China)

8681 1O **Study of overlay in EUV/ArF mix and match lithography** [8681-92]
C.-C. K. Huang, L. Chua, K. Hwang, A. Mani, G. Marcuccilli, B. Pierson, R. Karur-Shanmugam, J. C. Robinson, KLA-Tencor Corp. (United States); D. Choi, KLA-Tencor (Korea, Republic of); M. Ferber, K.-D. Roeth, KLA-Tencor (Germany); B. Lee, I. Lee, SK Hynix, Inc. (Korea, Republic of)

8681 1P **Lithography focus/exposure control and corrections to improve CDU** [8681-93]
Y.-K. Kim, M. Yelverton, J. Lee, J. Cheng, H. Wei, J. S. Kim, K. Gutjahr, GLOBALFOUNDRIES (United States); J. Gao, R. Karur-Shanmugam, P. Herrera, K. Huang, R. Volkovich, B. Pierson, KLA-Tencor Corp. (United States)

8681 1Q **Inspection of high aspect ratio layers at sub 20nm node** [8681-94]
A. Vikram, K. Lin, GLOBALFOUNDRIES (United States); J. Camp, S. Kini, F. Jin, V. Venkatesan, KLA-Tencor Corp. (United States)

8681 1R **Characterization of photochemical filtration membranes in organic solvents by using sub-10nm fluorescent Cd-based QDs** [8681-95]
S. Liu, H. Zhang, Entegris, Inc. (United States)

8681 1S **Scatterometry accuracy improvement using 3D shapes** [8681-96]
S. Zangooie, S. Myneni, P. Wilkens, HGST (United States); N. J. Keller, T. P. Sarathy, M. Tabet, Nanometrics Inc. (United States)

8681 1T **Advanced gate CDU control in sub-28nm node using poly slot process by scatterometry metrology** [8681-97]
W.-J. Tzai, H. Chen, J.-J. Lin, Y.-H. Huang, C.-C. Yu, United Microelectronics Corp. (Taiwan); C.-H. B. Lin, S. Yoo, C.-J. E. Huang, L. Mihardja, KLA-Tencor Corp. (United States)

8681 1V **The challenges encountered in the integration of an early test wafer surface scanning inspection system into a 450mm manufacturing line** [8681-99]
J. Lee, Global 450 Consortium (G450C) (United States); S. McGarvey, Hitachi High-Technology America, Inc. (United States)

8681 20 **Sub-40nm high-volume manufacturing overlay uncorrectable error evaluation** [8681-106]
P. Baluswamy, R. Khurana, B. Orf, W. Keller, Micron Technology, Inc. (United States)

8681 21 **Application of DBM tool for detection of EUV mask defect** [8681-16]
G. Yoo, J. Kim, C. Park, T. Lee, S. Ji, H. Yang, D. Yim, SK Hynix, Inc. (Korea, Republic of); B. Park, K. Maruyama, M. Yamamoto, NGR Inc. (Japan)

8681 22 **Computational defect review for actinic mask inspections** [8681-109]
P. Morgan, D. Rost, D. Price, MP Mask Technology Ctr., LLC (United States); N. Corcoran, M. Satake, P. Hu, D. Peng, D. Yonenaga, V. Tolani, Luminescent Technologies (United States)
### DESIGN-BASED METROLOGY FOR DEVELOPMENT AND MANUFACTURING APPLICATIONS

*P. Brooker, Synopsys, Inc.* (United States); M. Lee, E. V. Russel, Micron Technology, Inc. (United States); S. Levi, Applied Materials (Israel); S. Berthiaume, Synopsys, Inc. (Canada); W. A. Stanton, T. Brist, Synopsys, Inc. (United States)

### PRODUCTIVITY IMPROVEMENT THROUGH AUTOMATED OPERATION OF RETICLE DEFECT INSPECTION TOOLS IN A WAFER FAB ENVIRONMENT

*C. Holfeld, H. Wagner, GLOBALFOUNDRIES* (Germany); A. Tchikoulaeva, Lasertec U.S.A., Inc. Zweigniederlassung Deutschland (Germany); S. Leebeth, S. Melzig, GLOBALFOUNDRIES (Germany); Y. Zhang, Lasertec U.S.A., Inc. Zweigniederlassung Deutschland (Germany); S. Tanabe, T. Katoh, K. Moriiizumi, Lasertec Corp. (Japan)

### INTRODUCTION OF A HIGH THROUGHPUT SPM FOR DEFECT INSPECTION AND PROCESS CONTROL

*H. Sadeghian, N. B. Koster, T. C. van den Dool, TNO* (Netherlands)

### QUANTITATIVE CD-SEM RESIST SHRINKAGE STUDY AND ITS APPLICATION FOR ACCurate CD-SEM TOOLS’ MATCHING

*W. H. Li, Y. S. Lin, S. F. Yang, B. X. Cai, Y. Huang* Semiconductor Manufacturing International Corp. (China)

### POSTER SESSION: STUDENT POSTERS

<table>
<thead>
<tr>
<th>Poster Number</th>
<th>Title</th>
<th>Authors</th>
</tr>
</thead>
<tbody>
<tr>
<td>8681.29</td>
<td><strong>Phase extraction from random phase-shifted shadow moiré fringe patterns using stereovision technique</strong></td>
<td>F. Gu, H. Du, H. Zhao, B. Li, Xi’an Jiaotong Univ. (China)</td>
</tr>
<tr>
<td>8681.2A</td>
<td><strong>Fast phase shifting shadow moiré by utilizing multiple light sources</strong></td>
<td>H. Du, H. Zhao, B. Li, Xi’an Jiaotong Univ. (China)</td>
</tr>
<tr>
<td>8681.2B</td>
<td><strong>Measurement configuration optimization for grating reconstruction by Mueller matrix polarimetry</strong></td>
<td>X. Chen, S. Liu, C. Zhang, Huazhong Univ. of Science and Technology (China); H. Jiang, The Univ. of Texas at Arlington (United States)</td>
</tr>
</tbody>
</table>

### DSA METROLOGY AND INSPECTION: JOINT SESSION WITH CONFERENCES 8680 AND 8681

<table>
<thead>
<tr>
<th>Poster Number</th>
<th>Title</th>
<th>Authors</th>
</tr>
</thead>
<tbody>
<tr>
<td>8681.2C</td>
<td><strong>Application of optical CD metrology for alternative lithography</strong></td>
<td>M. Asano, A. Kawamoto, K. Matsuki, Toshiba Corp. (Japan); S. Godny, Nova Measuring Instruments Ltd. (Israel); T. Lin, K. Wakamoto, Nova Measuring Instruments K.K. (Japan)</td>
</tr>
<tr>
<td>8681.2D</td>
<td><strong>Hybrid approach to optical CD metrology of directed self-assembly lithography</strong></td>
<td>S. Godny, Nova Measuring Instruments Ltd. (Israel); M. Asano, A. Kawamoto, Toshiba Corp. (Japan); K. Wakamoto, Nova Measuring Instruments K.K. (Japan); K. Matsuki, Toshiba Corp. (Japan); C. Bozdog, M. Sendelbach, Nova Measuring Instruments Inc. (United States); I. Turovets, R. Urenski, R. Milo, Nova Measuring Instruments Ltd. (Israel)</td>
</tr>
</tbody>
</table>
OPTICAL EXTENSIONS

8681 2F  
**TSV reveal height and dimension metrology by the TSOM method** [8681-32]  
V. Vartanian, SEMATECH (United States); R. Attota, H. Park, G. Orji, National Institute of Standards and Technology (United States); R. A. Allen, SEMATECH (United States) and National Institute of Standards and Technology (United States)  

8681 2G  
**Use of TSOM for sub-11nm node pattern defect detection and HAR features** [8681-33]  
A. Arceo, B. Bunday, SEMATECH (United States); R. Attota, National Institute of Standards and Technology (United States)  

8681 2H  
**Robustness analysis of non-linear phase retrieval from single intensity measurement** [8681-34]  
A. Polo, S. F. Pereira, H. P. Urbach, Technische Univ. Delft (Netherlands)  

LER/LWR

8681 2I  
**Systematic errors in the measurement of power spectral density (Invited Paper)** [8681-35]  
C. A. Mack, Lithoguru.com (United States)  

8681 2J  
**Towards development of a sidewall roughness standard** [8681-36]  
A.CORDES, B. BUNDAY, SEMATECH (United States); S. Hand, J. Osborne, Bruker Nano Inc. (United States); H. Porter, GLOBALFOUNDRIES (United States)  

8681 2K  
**Roughness of EUV resists exposed to EUV, ArF and KrF radiation as evaluated using three tools: spectroscopic ellipsometry, AFM and SEM** [8681-37]  
B. C. Park, Y. J. Cho, Korea Research Institute of Standards and Science (Korea, Republic of); I. Kim, J. Yeo, SAMSUNG Electronics Co., Ltd. (Korea, Republic of)  

8681 2L  
**Evaluation of methods for noise-free measurement of LER/LWR using synthesized CD-SEM images** [8681-120]  
V. Constantoudis, National Ctr. for Scientific Research Demokritos (Greece); E. Pargon, LTM, CNRS (France)  

8681 2N  
**Key points to measure accurately an ultra-low LER by using CD-SEM** [8681-108]  
H. Kawada, T. Kawasaki, T. Ikegami, N. Hasegawa, Hitachi High-Technologies Corp. (Japan); K. Oyama, H. Yaegashi, Tokyo Electron Ltd. (Japan)  

OVERLAY

8681 2O  
**Diffraction based overlay and image based overlay on production flow for advanced technology node** [8681-40]  
Y. Blancquaert, CEA-LETI (France); C. Dezauzier, STMicroelectronics (France)  

8681 2P  
**Reduction of image-based ADI-to-AEI overlay inconsistency with improved algorithm** [8681-41]  
Fundamentals of overlay measurement and inspection using scanning electron-microscope [8681-42]
T. Kato, Y. Okagawa, O. Inoue, K. Arai, S. Yamaguchi, Hitachi High-Technologies Corp. (Japan)

DCM: device correlated metrology for overlay measurements [8681-43]
C. Chen, G. K. C. Huang, Y. C. Pai, J. C. H. Wu, Y. W. Cheng, S. C. C. Hsu, C. C. Yu, United Microelectronics Corp. (Taiwan); N. Amir, KLA-Tencor (Israel); D. Choi, KLA-Tencor (Korea, Republic of); T. Itzkovich, I. Tarshish-Shapir, KLA-Tencor (Israel); D. C. Tien, KLA-Tencor Corp. (United States); E. Huang, K. T. L. Kuo, KLA-Tencor (Taiwan); T. Kato, O. Inoue, H. Kawada, Y. Okagawa, Hitachi High-Technologies Corp. (Japan); L. Huang, M. Hsu, A. Su, Hitachi High-Technologies Taiwan Corp. (Taiwan)

In-die overlay metrology by using CD-SEM [8681-70]
O. Inoue, T. Kato, Y. Okagawa, H. Kawada, Hitachi High-Technologies Corp. (Japan)

Stress inspection for overlay characterization [8681-125]
D. M. Owen, Ultratech, Inc. (United States)

Multi layer overlay measurement recent developments [8681-126]
N. Amir, N. Shuall, I. Tarshish-Shapir, KLA-Tencor (Israel); P. Leray, IMEC (Belgium)

SEM, AFM, SPM

3D AFM method for characterization of resist effect of aerial image contrast on side wall roughness [8681-46]
Y.-H. Lee, S.-J. Cho, S.-I. Park, Park Systems Corp. (United States); R. Ayothi, Y. Hishiro, JSR Micro, Inc. (United States)

Three-dimensional profile extraction from CD-SEM image and top/bottom CD measurement by line-edge roughness analysis [8681-47]
A. Yamaguchi, T. Ohashi, Hitachi, Ltd. (Japan); T. Kawasaki, O. Inoue, H. Kawada, Hitachi High-Technologies Corp. (Japan)

Buckling characterization of gate all around silicon nanowires [8681-48]
S. Levi, I. Schwarzband, Y. Weinberg, R. Cornell, O. Adan, Applied Materials (Israel); G. M. Cohen, C. Cen, L. Gignac, IBM Thomas J. Watson Research Ctr. (United States)

Characterization of a 'first measurement effect' in CD-SEM measurement [8681-68]
B. Cai, Y.-S. Lin, Q. Wu, Y. Huang, S. Yang, W.-H. Li, M. Hao, Semiconductor Manufacturing International Corp. (China)

CROSS-TECHNOLOGY COMPARISONS, HYBRIDS, AND ACCURACY

Edge determination methodology for cross-section STEM image of photoresist feature used for reference metrology (Invited Paper) [8681-49]
K. Takamasu, H. Okitou, S. Takahashi, The Univ. of Tokyo (Japan); M. Konno, O. Inoue, H. Kawada, Hitachi High-Technologies Corp. (Japan)
Characterizing edge profiles of photomask structures with complementary information from SEM and AFM [8681-50]
W. Häßler-Grohne, D. Hüser, Physikalisch-Technische Bundesanstalt (Germany)

High accuracy CD matching monitor for CD-SEM beyond 20nm process [8681-82]
K. Ueda, T. Mizuno, K. Setoguchi, Hitachi High-Technologies Corp. (Japan)

**PROCESS CONTROL**

In-field in-design metrology target integration for advanced CD and overlay process control via DoseMapper and high order overlay correction for 28nm and beyond logic node [8681-52]

CD optimization methodology for extending optical lithography [8681-53]
C. Wong, G. Seevaratnam, T. Wiltshire, N. Felix, T. Brunner, P. Rawat, IBM Corp. (United States); M. Escalante, ASML Netherlands B.V. (Netherlands); W. Kim, E. Rottenkolber, ASML USA Inc. (United States); A. Elmalk, V. Wang, C. Leewis, P. Hinnen, ASML Netherlands B.V. (Netherlands)

Improvement of focus accuracy on processed wafer [8681-54]
S. Higashibata, N. Komine, K. Fukuhara, T. Koike, Y. Kato, K. Hashimoto, Toshiba Corp. (Japan)

An investigation of high-order process correction models and techniques to improve overlay control by using multiple-pass cascading analysis at an advanced technology node [8681-56]
M. Z. Ullah, M. F. M. Jazim, S. Tran, A. Qi, D. Goh, Micron Semiconductor Asia Pte. Ltd. (Singapore); J. Ang, D. Goh, KLA-Tencor (Singapore); D. Tien, K. Huang, KLA-Tencor Corp. (United States); D. Choi, KLA-Tencor (Korea, Republic of)

**LATE BREAKING NEWS**

Gaps analysis for CD metrology beyond the 22nm node (Invited Paper) [8681-57]
B. Bunday, SEMATECH (United States); T. A. Germer, National Institute of Standards and Technology (United States); V. Vartanian, A. Cordes, SEMATECH (United States); A. Cepler, SEMATECH (United States) and Univ. at Albany (United States); C. Settens, Univ. at Albany (United States)

High-speed atomic force microscopy for patterned defect review [8681-100]

Metrology solutions for high performance germanium multi-gate field-effect transistors using optical scatterometry [8681-107]
H.-C. Chin, M.-L. Ling, Nanometrics Inc. (United States); B. Liu, X. Zhang, National Univ. of Singapore (Singapore); J. Li, Y. Liu, J. Hu, Nanometrics Inc. (United States); Y.-C. Yeo, National Univ. of Singapore (Singapore)
Enhancing metrology by combining spatial variability and global inference
C. J. Spanos, J. Y. Baek, Univ. of California, Berkeley (United States)

Performance-based metrology of critical device performance parameters for in-line non-contact high-density intra-die monitor/control on a 32nm SOI advanced logic product platform
M. M. Pelella, tau-Metrix, Inc. (United States); A. C. Mocuta, IBM Corp. (United States); B. Lee, tau-Metrix, Inc. (United States); N. Zamdmer, D. K. Slisher, X. Yu, IBM Corp. (United States); J. S. Vickers, tau-Metrix, Inc. (United States); Y. Tsuruta, Tokyo Electron America Inc. (United States); S. S. Iyer, IBM Corp. (United States); N. Pakdaman, tau-Metrix, Inc. (United States)

Author Index
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Yi-sha Ku, Industrial Technology Research Institute (Taiwan)
Byoung-Ho Lee, SAMSUNG Electronics Company, Ltd. (Korea, Republic of)
Christopher J. Raymond, Nanometrics Inc. (United States)
John C. Robinson, KLA-Tencor Corporation (United States)
Martha I. Sanchez, IBM Almaden Research Center (United States)
Matthew J. Sendelbach, Nova Measuring Instruments, Inc. (United States)
Richard M. Silver, National Institute of Standards and Technology (United States)
Costas J. Spanos, University of California, Berkeley (United States)
Vladimir A. Ukraintsev, Nanometrology International, Inc. (United States)
Alok Vaid, GLOBALFOUNDRIES Inc. (United States)
Session Chairs

Keynote Session
Alexander Starikov, I&I Consulting (United States)
Jason P. Cain, Advanced Micro Devices, Inc. (United States)

Metrology for Process Control
Masafumi Asano, Toshiba Corporation (Japan)
John C. Robinson, KLA-Tencor Corporation (United States)

Design-based Metrology and Process Control
Jason P. Cain, Advanced Micro Devices, Inc. (United States)
Shunsuke Koshihara, Hitachi High-Technologies Corporation (Japan)

Inspection
Benjamin D. Bunday, SEMATECH North (United States)
Timothy F. Crimmins, Intel Corporation (United States)

Accelerated Development of Materials and Processes: Joint Session with Conference 8681 and 8682
Clifford L. Henderson, Georgia Institute of Technology (United States)
Martha I. Sanchez, IBM Almaden Research Center (United States)

New Horizons
Richard M. Silver, National Institute of Standards and Technology (United States)
Costas J. Spanos, University of California, Berkeley (United States)

Scatterometry
Richard M. Silver, National Institute of Standards and Technology (United States)
Alok Vaid, GLOBALFOUNDRIES Inc. (United States)

Poster Session
John C. Robinson, KLA-Tencor Corporation (United States)
Matthew J. Sendelbach, Nova Measuring Instruments Inc. (United States)

DSA Metrology and Inspection: Joint Session with Conferences 8680 and 8681
Joy Y. Cheng, IBM Almaden Research Center (United States)
Martha I. Sanchez, IBM Almaden Research Center (United States)

Optical Extensions
Matthew J. Sendelbach, Nova Measuring Instruments, Inc. (United States)
Timothy F. Crimmins, Intel Corporation (United States)
LER/LWR

Benjamin D. Bunday, SEMATECH North (United States)
Byoung-Ho Lee, SAMSUNG Electronics Company, Ltd.
   (Korea, Republic of)

Overlay

Ofer Adan, Applied Materials (Israel)
Christopher J. Raymond, Nanometrics Inc. (United States)

SEM, AFM, SPM
Matthew J. Sendelbach, Nova Measuring Instruments Inc.
   (United States)
Vladimir A. Ukraintsev, Nanometrology International, Inc.
   (United States)

Cross-technology Comparisons, Hybrids, and Accuracy

Vladimir A. Ukraintsev, Nanometrology International, Inc.
   (United States)
Chih-Ming Ke, Taiwan Semiconductor Manufacturing Company Ltd.
   (Taiwan)

Process Control
Masafumi Asano, Toshiba Corporation (Japan)
Alok Vaid, GLOBALFOUNDRIES Inc. (United States)

Late Breaking News
Ofer Adan, Applied Materials (Israel)
Alexander Starikov, I&I Consulting (United States)
Introduction

The 27th conference on Metrology, Inspection, and Process Control for Microlithography was noted for successful exchange of ideas, discussion of challenges and opportunities, and for free-flowing networking with some of the top professionals in the field. Direct engagement and effective dialog with metrology customers across all other conferences at the Advanced Lithography Symposium was instrumental in the increased popularity and the growth of this conference.

One good example of this is the success of joint sessions with other conferences. This year there were two such sessions.

SESSION 5: Accelerated Development of Materials and Processes: Joint Session with Conference 8681 and 8682, a joint session with the conference on Advances in Resist Materials and Processing Technology. Chaired by Clifford L. Henderson and Martha I. Sanchez, this session included presentations on novel uses of metrology technology for characterizing various aspects of photoresist materials:

- “In situ dissolution analysis of half-pitch line and space patterns at various resist platforms using high-speed atomic force microscopy,” Julius Joseph S. Santillan, Toshiro Itani [8682-17]
- “Mechanisms of resist pattern size shrinkage caused by electron beam,” Seiichi Tagawa, Cong Que Dinh, Satoshi Enomoto, Akihiro Oshima
- “Photoresist shrinkage effects in 16nm node extreme ultraviolet (EUV) photoresist targets,” Benjamin Bunday, Cecilia Montgomery, Warren Montgomery, Aron Cepler [8681-18]
- “Precise measurement of photoresist cross-sectional shape change caused by SEM-induced shrinkage,” Takeyoshi Ohashi, Tomoko Sekiguchi, Atsuko Yamaguchi, Junichi Tanaka, Hiroki Kawada [8681-19]

SESSION 8: DSA Metrology and Inspection: Joint Session with Conferences 8680 and 8681, a joint session with the conference on Alternative Lithographic Technologies. Back by popular demand and chaired once again by Joy Y. Cheng and Martha I. Sanchez, this joint session covered applications in the emerging field of directed self-assembly (DSA):

- “Defect source analysis of directed self-assembly process (DSA of DSA)” (Invited Paper), Paulina Rincon Delgadillo, Ryota Harukawa, Mayur Suri, Stephane Durant, Andrew Cross, Venkat R. Nagaswami, Dieter Van Den Heuvel, Roel Gronheid, Paul Nealey [8680-20]
- “Application of optical CD metrology for alternative lithography,” Masafumi Asano, Akiko Kawamoto, Kazuto Matsuki, Stephane Godny, Tingsheng Lin, Koichi Wakamoto [8681-29]
With nine Keynote/Invited Papers in 2013, the most promising and broadly appealing papers are given the highest visibility and attention. In addition, the best papers of the metrology conference are recognized with the Best Paper Awards.

Starting in 2002, the Diana Nyyssonen Memorial Award has been given each year to the best published paper of the past year conference as selected by the conference program committee. This year, Hitachi High-Technologies America established a generous multi-year sponsorship of the Diana Nyyssonen Memorial Award, adding an honorarium to this prestigious award and we are very grateful for their support.

New this year is the Best Student Paper Award. Established through a generous multi-year sponsorship from KLA-Tencor, this award also features an SPIE citation and an honorarium for the winner. The best student paper is selected by the panel of judges composed of members of the conference program committee, as well as representatives from the National Institute of Standards and Technology (NIST). The Best Student Paper Award judges in 2013 were: Brian Barnes (NIST), Ben Bunday (SEMATECH North), Tim Crimmins (Intel Corp.), Mike Postek (NIST), Matt Sendelbach (Nova Measuring Instruments), Rick Silver (NIST), Costas Spanos (University of California, Berkeley), Alok Vaid (GLOBALFOUNDRIES, Inc.), and John Villarrubia (NIST). Special thanks are also due to John Robinson of KLA-Tencor for coordinating the award-related logistics, enabling smooth on-site student paper evaluations by the judges and selection of the winner, culminating with the Award Ceremony on the last day of the conference.

The winner of the Best Student Paper award at Metrology, Inspection, and Process Control for Microlithography XXVII is Gangadhara Raja Muthinti from University at Albany for his paper 8681-21, “Mueller-based scatterometry measurement of nanoscale structures with anisotropic in-plane optical properties,” co-authored with Manasa Medikonda, Jody Fronheiser, Vimal K. Kamineni, Brennan J. Peterson, Joseph Race, and Alain C. Diebold. Congratulations!

Alexander Starikov
Jason P. Cain
The Diana Nyyssonen Memorial Award for Best Paper

Diana Nyyssonen was a pioneer in the field of dimensional metrology. Her early interests in optics were formed under the tutelage of Professor Edward L. O'Neill at Boston University. In 1965, she went to work for Brian J. Thompson and George B. Parrent, Jr. at Technical Operations, Inc., Burlington, Massachusetts. Diana’s knowledge of physical optics and related modeling grew rapidly as she worked on the teams developing the theory of partially coherent imaging, physical models, equipment and applications for the U.S. government, astronomy, and industry. In addition to Brian J. Thompson and George B. Parrent, Diana’s professional circle at that time included George O. Reynolds, John B. DeVelis, Adriaan Walther, Philip S. Considine, Richard J. Becherer, and Richard E. Swing.

In 1969, Diana Nyyssonen joined the Image Optics and Photography Section of the Metrology Division at the National Bureau of Standards (NBS), initially working for Calvin S. McCamy on microdensitometry, then on linewidth measurements for integrated circuit manufacturing applications. Sponsored by NBS, Diana also attended the Institute of Optics, University of Rochester at Rochester, New York where Professor B. J. Thompson, Director of the Institute, was her advisor. She completed her Ph.D. in 1975, with her Thesis “High resolution microdensitometry of photographic emulsions” establishing the scientific foundations and the outlook of the things to come. Dr. Nyyssonen’s modeling of thin films observed by an optical microscope demonstrated that line (space) width smaller than Rayleigh resolution limit can be measured. She produced linewidth measurements in photomasks with calibration based on physical modeling and first principles, establishing the first critical dimension standards for the microelectronics industry and the foundation of today’s dimensional metrology.

Dr. Nyyssonen left NBS in 1985 to form her own metrology company then joined IBM at East Fishkill, New York in 1988. Continuing the development of accurate optical modeling of imaging of thick films with Christopher P. Kirk, NBS and other teams, she started projects on metrology with scatterometry and interference microscopy, modeled imaging in low voltage CD-SEM, and spearheaded the establishment of CD-AFM.

Diana Nyyssonen’s personal contributions to the field of dimensional metrology, as well as her collaborations and mentorships in the industry, consortia, and academia, accelerated and influenced the development of basic technology and metrology applications with optical microscopy and scatterometry, SEM, and AFM.

Metrology, Inspection, and Process Control for Microlithography is the leading international forum for the discussion and presentation of technical advances in the broader field of semiconductor metrology. The Diana Nyyssonen Memorial Award for the Best Paper at this Conference recognizes the most significant current contributions.
Due to the Conference's long history, significant attendance and high paper counts, to win this Award requires a very significant new contribution to the field. The selection of the best paper is initiated during the Conference by nomination, followed by extensive review by the Program Committee. It is based on both the technical merit and persuasiveness of the oral presentation and the overall quality of the published paper. Past award winners include leading international researchers in the area of semiconductor metrology and process control whose contributions have fundamentally improved the way semiconductors are manufactured.

We are pleased to honor the winners of the Diana Nyyssonen Memorial Award for the Best Paper of 2012, as well as those who have won in previous years:

2012

2011

2010

2009

2008

2007

2006

2005
2004

2003

2002

2001